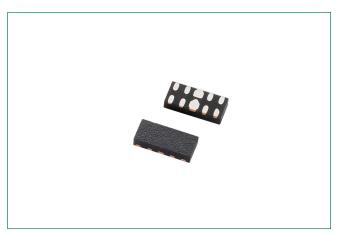
SP33R6

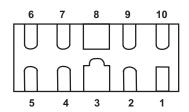
0.2pF, 12kV, 0.6V Breakdown Avalanche Diode for Ultra High Speed Interfaces





Note: This package image is for example and reference only. for detail package drawing, please refer to the package section in this datasheet.

Pinout



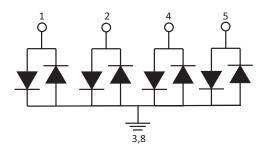
Description

Benchmark setting breakdown voltage performance, protecting sub 20 nm I/O's. Finer geometry chip designs run the risk of damage at voltage levels higher than 3.3V. The SP33R6 is a breakdown avalanche diode for ultra high speed interfaces and it provides headroom to support all of the low voltage differential signaling (0.3V) while protecting the data lines from damaging overvoltage, starting at 0.6V.

Features

- ESD, IEC 61000-4-2, ±12kV contact, ±15kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5, 2nd Edition, 3A (8/20us)
- Low capacitance of 0.2pF (TYP) per I/O
- Halogen-free, lead-free and RoHS compliant

Functional Block Diagram



Note: pin6,7,9,10 are N.C

Applications

- USB 3.2, USB 4.0
- Thunderbolt 3.0
- PCIE

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I _{PP}	Peak Current (t _p =8/20µs)	3	А
T_OP	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

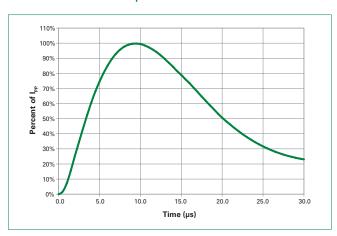
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units	
Reverse Standoff Voltage	V _{RWM}	$I_R = 1 \mu A$			0.3	V	
Breakdown Voltage V _{BR}		I _R =1mA	0.6		0.9	V	
Reverse Leakage Current I _{LEAK}		V_R =0.3V, Any I/O to GND			100	nA	
Clamp Voltage ¹	V _C	$I_{pp} = 1A$, $t_p = 8/20 \mu s$		2.5		V	
		$I_{pp} = 2A, t_p = 8/20 \mu s$		3.3			
Dynamic Resistance ³ R _{DYN}		TLP, $t_p = 100$ ns		0.3		Ω	
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±12			kV	
		IEC 61000-4-2 (Air Discharge)	±15			kV	
Line Capacitance ^{1, 2}	C_{L}	Reverse Bias=0V, f=3GHz		0.2		pF	

Note 1: Parameter is guaranteed by design and/or component characterization.

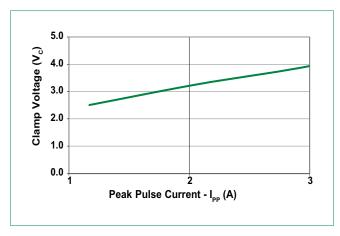
Note 2: Test equipment accuracy ±50fF.

Note 3: Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2=90ns

8/20µs Pulse Waveform



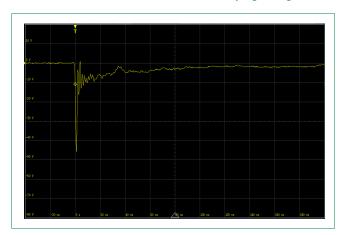
Clamping Voltage vs I_{pp}



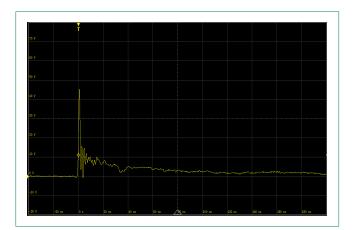


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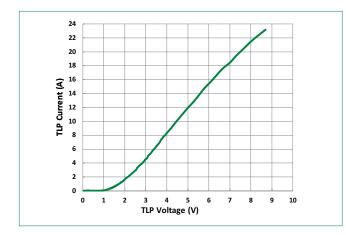
IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



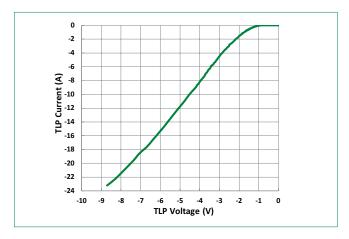
IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage



Positive Transmission Line Pulsing (TLP) Plot



Negative Transmission Line Pulsing (TLP) Plot



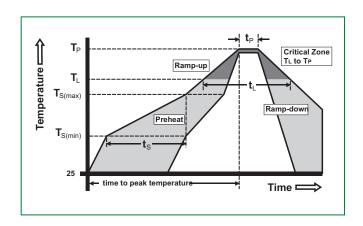


Soldering Perameters

Reflow Condition		Pb — Free assembly	
Pre Heat	- Temperature Min (T _{s(min)})	150°C	
	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 - 120 secs	
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max	
T _{S(max)} to T _L	- Ramp-up Rate	3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 - 150 seconds	
Peak Temperature (T _P)		260 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (t _p)		30 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T _p)		8 minutes Max.	
Do not exceed		260°C	

Ordering Information

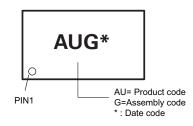
Part Number	Package	Min. Order Qty.
SP33R6-04UTG	μDFN-10	3000



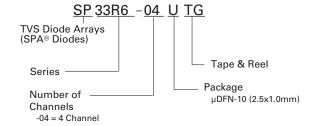
Product Characteristics

Lead Plating	PPF or Tin	
Lead material	Copper Alloy	
Substrate Material	Silicon	
Body Material	Molded Compound	
Flammability	UL Recognized compound meeting flammability rating V-0	

Part Marking System



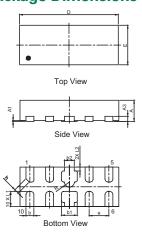
Part Numbering System

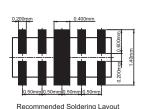




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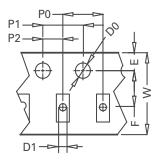
Package Dimensions — μ DFN-10 (2.5x1.0x0.5mm)

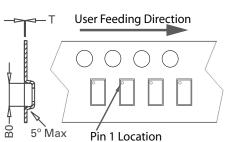


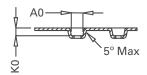


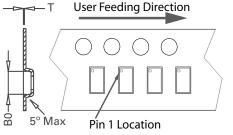
	Millimeters		Inches		
Symbol	Min	Max	Min	Max	
Α	0.50	0.60	0.020	0.024	
A1	0.00	0.05	0.000	0.002	
A3	0.125	0.175	0.005	0.007	
b	0.15	0.25	0.006	0.010	
b1	0.35	0.45	0.014	0.018	
b2	0.20	0.30	0.008	0.012	
D	2.45	2.55	0.096	0.100	
E	0.95	1.05	0.037	0.041	
L1	0.28	0.48	0.011	0.019	
L2	0.05	0.15	0.002	0.006	
е	0.500 BASIC 0.125 REF		0.020 BASIC 0.005 REF		
R					
h	0.08	0.16	0.003	0.006	

Embossed Carrier Tape & Reel Specification — µDFN-10

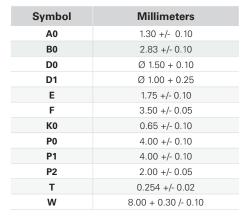


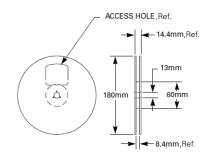












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